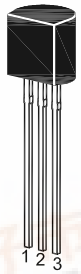
ST 2SA1024

PNP Silicon Epitaxial Planar Transistor

for high voltage applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	150	V
Collector Emitter Voltage	$-V_{CEO}$	150	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	50	mA
Emitter Current	I_E	50	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 5 V, $-I_C$ = 10 mA	Current Gain Group O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
Collector Base Cutoff Current at $-V_{CB}$ = 150 V		$-I_{CBO}$	-	-	0.1	µA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V		$-I_{EBO}$	-	-	0.1	µA
Collector Emitter Saturation Voltage at $-I_C$ = 10 mA, $-I_B$ = 1 mA		$-V_{CE(sat)}$	-	-	0.8	V
Base Emitter Voltage at $-V_{CE}$ = 5 V, $-I_C$ = 30 mA		$-V_{BE}$	-	-	0.9	V
Gain Bandwidth Product at $-V_{CE}$ = 30 V, $-I_C$ = 10 mA		f_T	-	120	-	MHz
Output Capacitance at $-V_{CB}$ = 10 V, f = 1 MHz		C_{OB}	-	-	5	pF